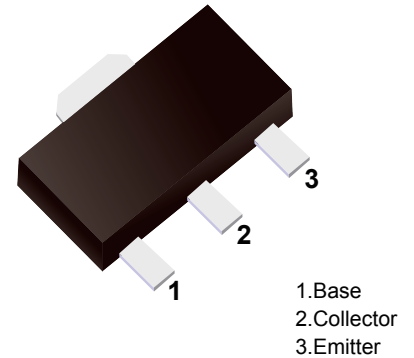


2SC3357

■ NPN Transistors

■ Features

- Low noise and high gain
- High power gain
- Large P_{tot}



■ Simplified outline(SOT-89)

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	20	V
Collector - Emitter Voltage	V_{CEO}	12	
Emitter - Base Voltage	V_{EBO}	3	
Collector Current - Continuous	I_C	100	mA
Collector Power Dissipation	P_C	1.2	W
Junction to Ambient Resistance	$R_{th(j-a)}$	62.5	$^\circ\text{C}/\text{W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to 150	

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	$I_C = 100 \mu\text{A}, I_E = 0$	20			V
Collector- emitter breakdown voltage	V_{CEO}	$I_C = 1 \text{ mA}, I_B = 0$	12			
Emitter - base breakdown voltage	V_{EBO}	$I_E = 100 \mu\text{A}, I_C = 0$	3			
Collector-base cut-off current	I_{CBO}	$V_{CB} = 20\text{V}, I_E = 0$			1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 3\text{V}, I_C = 0$			1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 50 \text{ mA}, I_B = 5 \text{ mA}$			0.4	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = 50 \text{ mA}, I_B = 5 \text{ mA}$			1.2	
DC current gain (Note.1)	h_{FE}	$V_{CE} = 10\text{V}, I_C = 20 \text{ mA}$	50		250	
Insertion Power Gain	$ S_{21e} ^2$	$V_{CE} = 10\text{V}, I_C = 20 \text{ mA}, f = 1 \text{ GHz}$		9		dB
Noise Figure	NF	$V_{CE} = 10\text{V}, I_C = 7 \text{ mA}, f = 1 \text{ GHz}$		1.1		
		$V_{CE} = 10\text{V}, I_C = 40 \text{ mA}, f = 1 \text{ GHz}$		1.8	3	
Reverse Transfer Capacitance	C_{re}	$V_{CB} = 10\text{V}, I_E = 0, f = 1 \text{ MHz}$			1	pF
Transition frequency	f_T	$V_{CE} = 10\text{V}, I_C = 20 \text{ mA}$		6.5		GHz

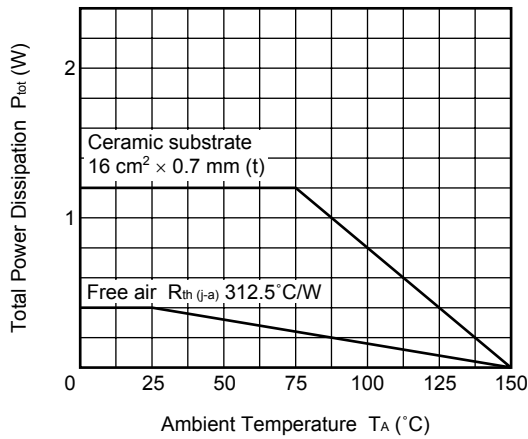
Note.1: Pulse measurement: $PW \leq 350 \mu\text{s}$, Duty Cycle $\leq 2\%$

■ Classification of h_{FE}

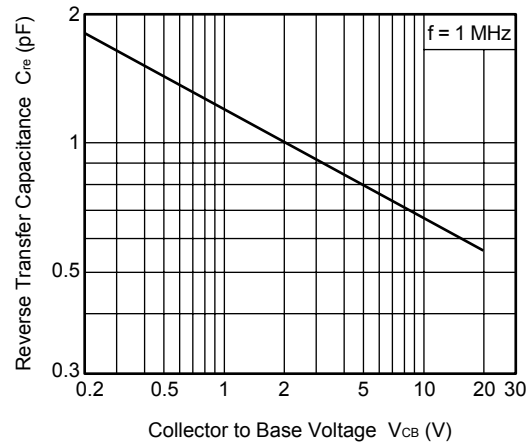
Type	2SC3357-F	2SC3357-E
Range	80-160	125-250
Marking	RF	RE

■ Typical Characteristics

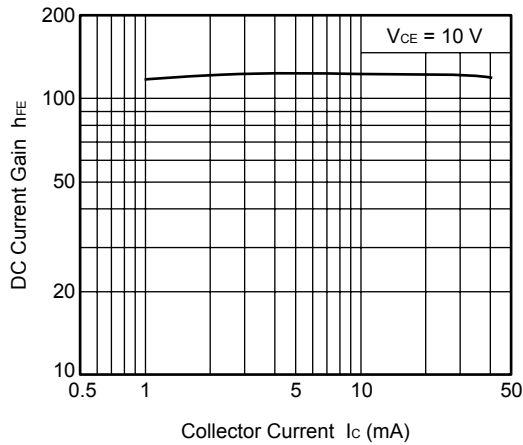
TOTAL POWER DISSIPATION
vs. AMBIENT TEMPERATURE



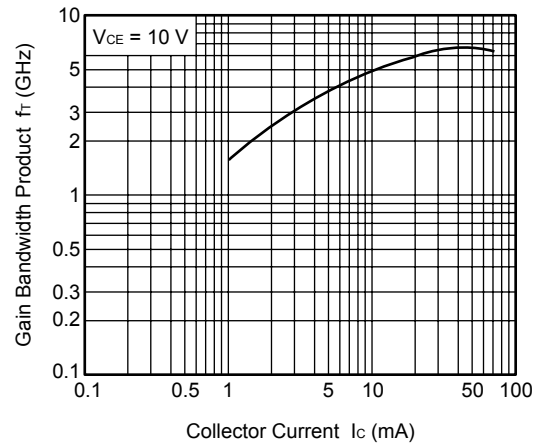
REVERSE TRANSFER CAPACITANCE
vs. COLLECTOR TO BASE VOLTAGE



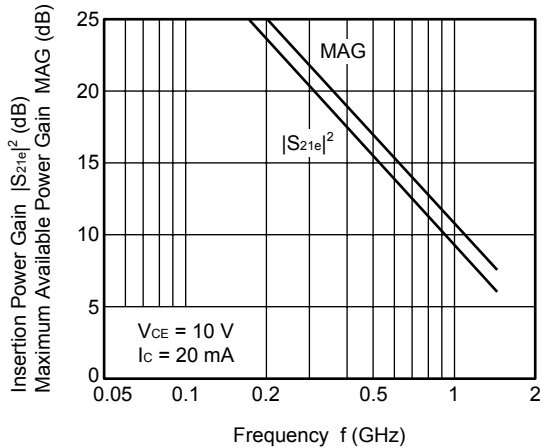
DC CURRENT GAIN vs.
COLLECTOR CURRENT



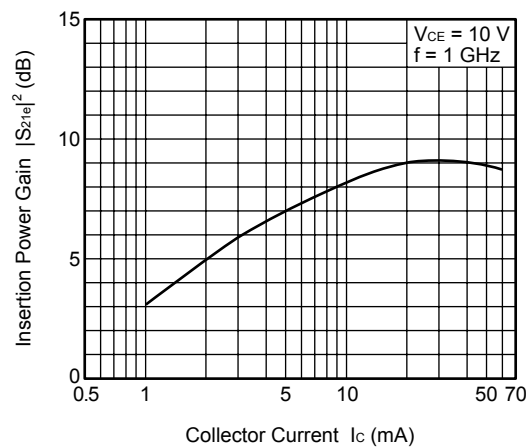
GAIN BANDWIDTH PRODUCT
vs. COLLECTOR CURRENT



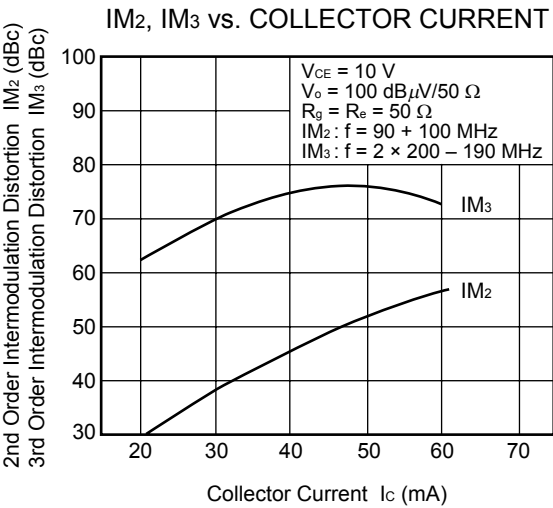
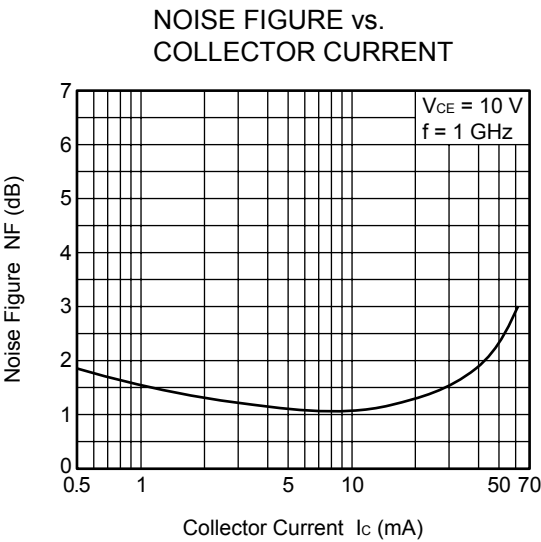
INSERTION POWER GAIN, MAG
vs. FREQUENCY



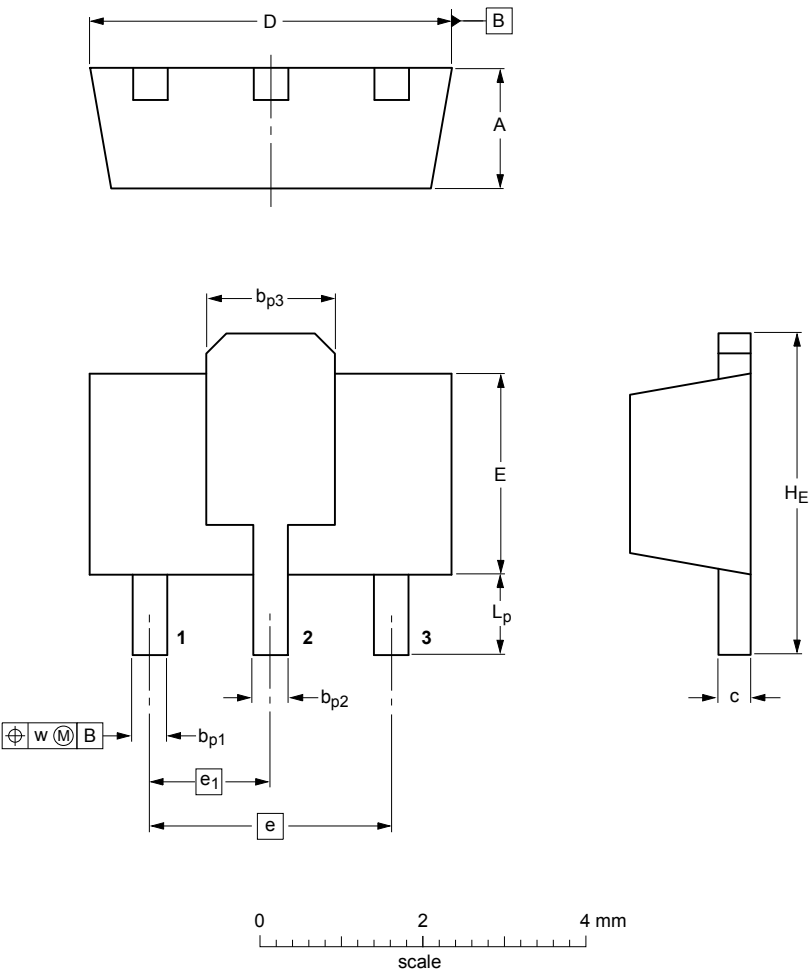
INSERTION POWER GAIN
vs. COLLECTOR CURRENT



■ Typical Characteristics



■ SOT-89



DIMENSIONS (mm are the original dimensions)

UNIT	A	b _{p1}	b _{p2}	b _{p3}	c	D	E	e	e ₁	H _E	L _p	w
mm	1.6 1.4	0.48 0.35	0.53 0.40	1.8 1.4	0.44 0.23	4.6 4.4	2.6 2.4	3.0	1.5	4.25 3.75	1.2 0.8	0.13